

## **isc** Silicon NPN Power Transistor

# MJB3055

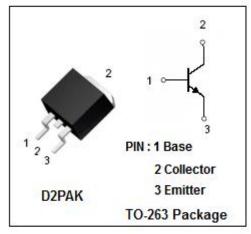
#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
- :  $V_{(BR)CEO} = 60V(Min)$
- · High DC Current Gain-
- : h<sub>FE</sub>= 20-100@I<sub>C</sub>= 4A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**



• Designed for use in general-purpose amplifier and switching applications.

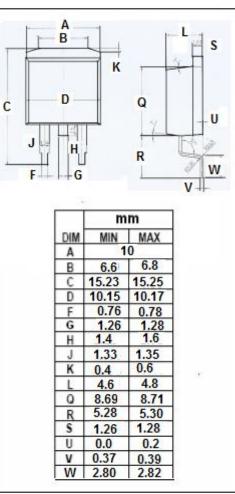


## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	70	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	10	Α	
Ι <sub>Β</sub>	Base Current-Continuous	6	Α	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C 75		W	
TJ	Junction Temperature 150		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range -55~150		$^{\circ}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.67	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	60			V
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A			1.1	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 3.3A			8.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 4A; V <sub>CE</sub> = 4V			1.8	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> = 0			0.7	mA
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 70V; I <sub>E</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 4V	20		100	
h <sub>FE-2</sub>	DC Current Gain	Ic= 10A; VcE= 4V	5			
f <sub>T</sub>	Current Gain-Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V; f= 500kHz	2.0			MHz

#### **NOTICE:**

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